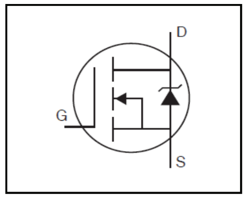
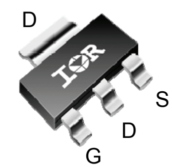
HEXFET® Power MOSFET

Features

- Advanced Process Technology
- Ultra Low On-Resistance
- Logic Level Gate Drive
- 150°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified *



V_{DSS}		55V
$R_{DS(on)}$	typ.	48mΩ
	max.	60mΩ
I_D		5.0A



SOT-223
AUIRLL024Z

G	D	S
Gate	Drain	Source

Description

Specifically designed for Automotive applications, this HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this design are a junction operating temperature, fast switching speed and improved repetitive avalanche rating . These features combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications.

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
AUIRLL024Z	SOT-223	Tape and Reel	2500	AUIRLL024ZTR

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (TA) is 25°C, unless otherwise specified.

Symbol	Parameter	Max.	Units
I_D @ T_A = 25°C	Continuous Drain Current, V_{GS} @ 10V ⑦	5.0	A
I_D @ T_A = 70°C	Continuous Drain Current, V_{GS} @ 10V ⑦	4.0	
I_{DM}	Pulsed Drain Current ①	40	
P_D @T_A = 25°C	Maximum Power Dissipation (PCB Mount) ⑦	2.8	W
P_D @T_A = 25°C	Maximum Power Dissipation (PCB Mount) ⑧	1.0	
	Linear Derating Factor (PCB Mount) ⑦	0.02	W/°C
V_{GS}	Gate-to-Source Voltage	± 16	V
E_{AS}	Single Pulse Avalanche Energy (Thermally Limited) ②	21	mJ
$E_{AS\ (Tested)}$	Single Pulse Avalanche Energy (Tested Value) ⑥	38	
I_{AR}	Avalanche Current ①	See Fig. 12a, 12b, 15, 16	A
E_{AR}	Repetitive Avalanche Energy ⑤		mJ
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount, steady state) ⑦	——	45	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount, steady state) ⑧	——	120	

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*Qualification standards can be found at www.infineon.com

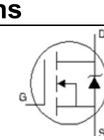
Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	55	—	—	V	V_{GS} = 0V, I_D = 250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.049	—	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	48	60	mΩ	V_{GS} = 10V, I_D = 3.0A ③
		—	—	80		V_{GS} = 5.0V, I_D = 3.0A ③
		—	—	100		V_{GS} = 4.5V, I_D = 3.0A ③
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	3.0	V	V_{DS} = V_{GS}, I_D = 250µA
gfs	Forward Trans conductance	7.5	—	—	S	V_{DS} = 25V, I_D = 3.0A
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	µA	V_{DS} = 55V, V_{GS} = 0V
		—	—	250		V_{DS} = 55V,V_{GS} = 0V,T_J = 125°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	200	nA	V_{GS} = 16V
	Gate-to-Source Reverse Leakage	—	—	-200		V_{GS} = -16V

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

Q_g	Total Gate Charge	—	7.0	11	nC	I_D = 3.0A
Q_{gs}	Gate-to-Source Charge	—	1.5	—		V_{DS} = 44V
Q_{gd}	Gate-to-Drain Charge	—	4.0	—		V_{GS} = 5.0V ③
$t_{d(on)}$	Turn-On Delay Time	—	8.6	—	ns	V_{DD} = 28V
t_r	Rise Time	—	33	—		I_D = 3.0A
$t_{d(off)}$	Turn-Off Delay Time	—	20	—		R_G = 56Ω
t_f	Fall Time	—	15	—		V_{GS} = 5.0V ③
C_{iss}	Input Capacitance	—	380	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	66	—		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	—	36	—		f = 1.0MHz
C_{oss}	Output Capacitance	—	220	—		V_{GS} = 0V, V_{DS} = 1.0V,f = 1.0MHz
C_{oss}	Output Capacitance	—	53	—		V_{GS} = 0V, V_{DS} = 44V,f = 1.0MHz
$C_{oss\ eff.}$	Effective Output Capacitance	—	93	—		V_{GS} = 0V, V_{DS} = 0V to 44V ④

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	5.0	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	40		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	T_J = 25°C,I_S = 3.0A,V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	—	15	23	ns	T_J = 25°C ,I_F = 3.0A, V_{DD} = 28V
Q_{rr}	Reverse Recovery Charge	—	9.1	14	nC	di/dt = 100A/µs ③
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
② Limited by T_{Jmax}, Starting T_J = 25°C, L = 4.8mH, R_G = 25Ω, I_{AS} = 3.A. V_{GS} = 10V.Part not recommended for use above this value.
③ Pulse width ≤ 1.0ms; duty cycle ≤ 2%.
④ $C_{oss\ eff.}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.
⑤ Limited by T_{Jmax} , see Fig.12a, 12b, 15, 16 for typical repetitive avalanche performance.
⑥ This value determined from sample failure population, starting T_J = 25°C, L = 4.8mH, R_G = 25Ω, I_{AS} = 3.0A, V_{GS} =10V.
⑦ When mounted on 1 inch square copper board.
⑧ When mounted on FR-4 board using minimum recommended footprint.

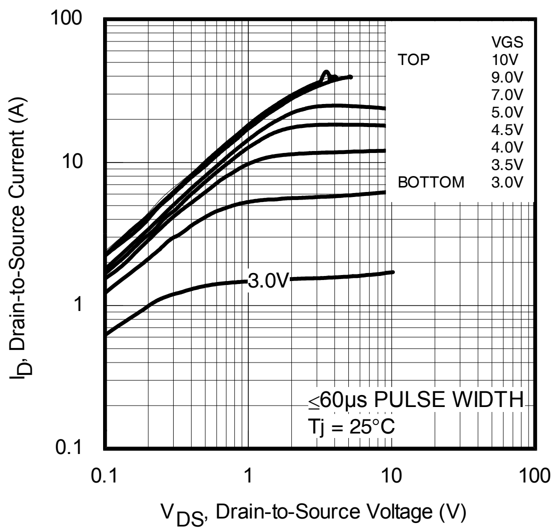


Fig. 1 Typical Output Characteristics

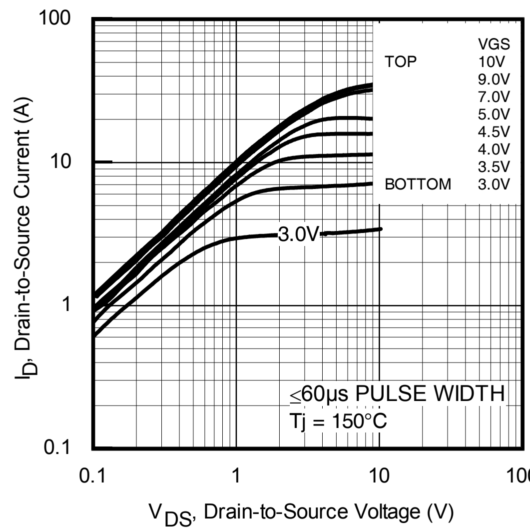


Fig. 2 Typical Output Characteristics

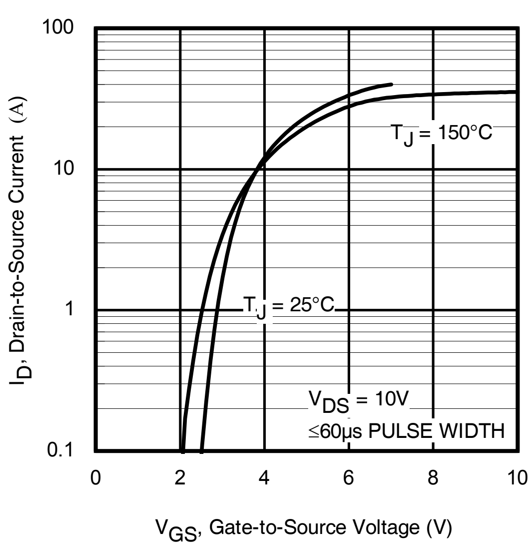


Fig. 3 Typical Transfer Characteristics

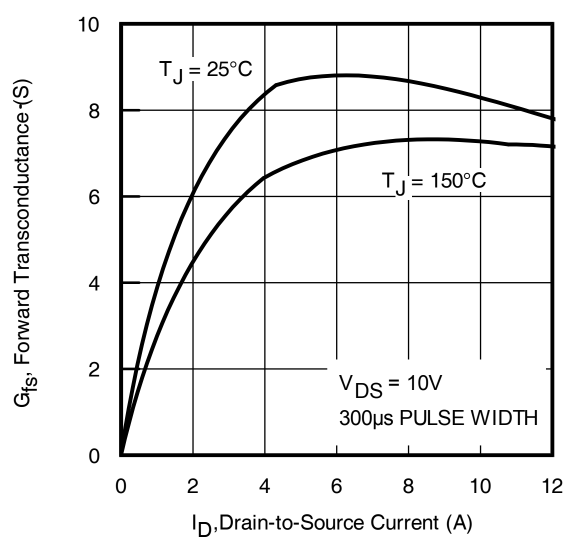


Fig. 4 Typical Forward Trans conductance vs. Drain Current

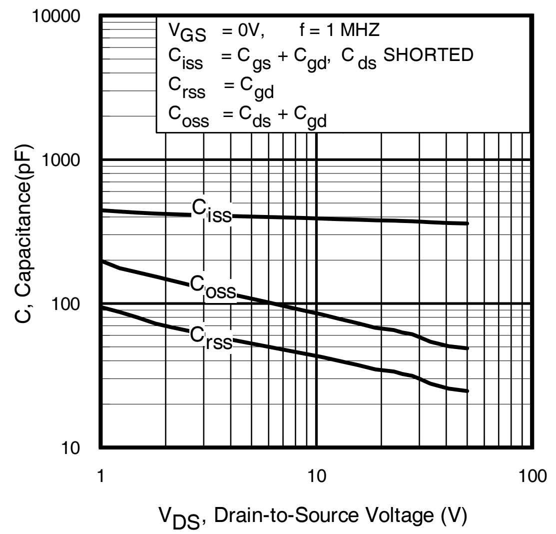


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

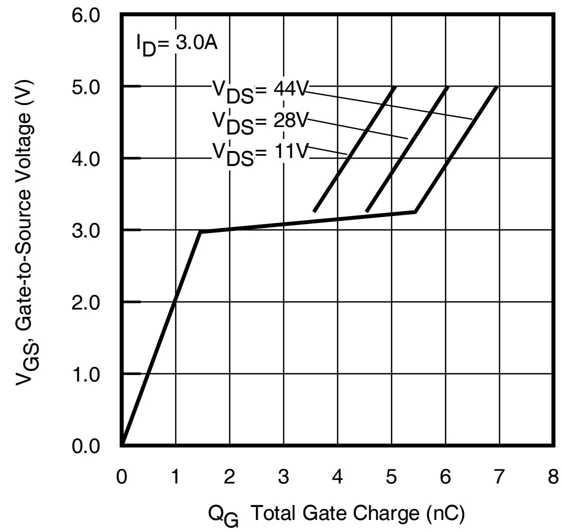


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

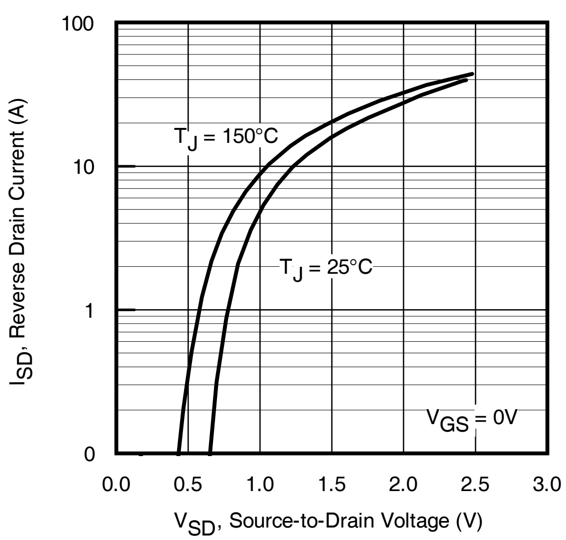


Fig. 7 Typical Source-to-Drain Diode Forward Voltage

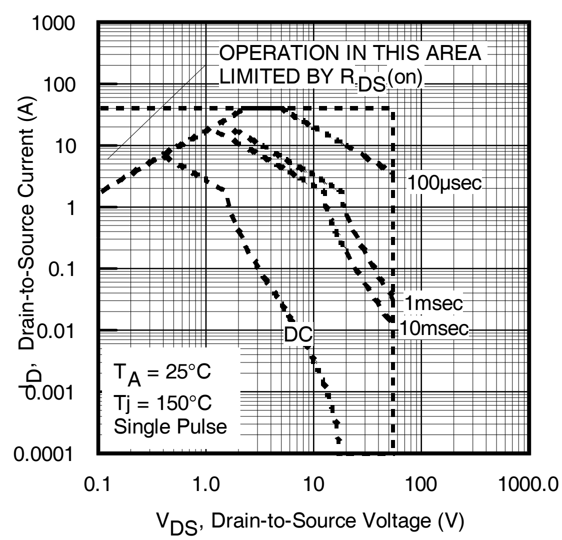


Fig 8. Maximum Safe Operating Area

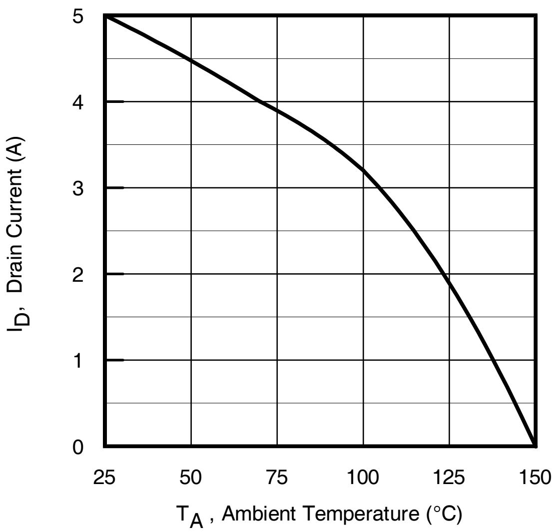


Fig 9. Maximum Drain Current Vs. Ambient Temperature

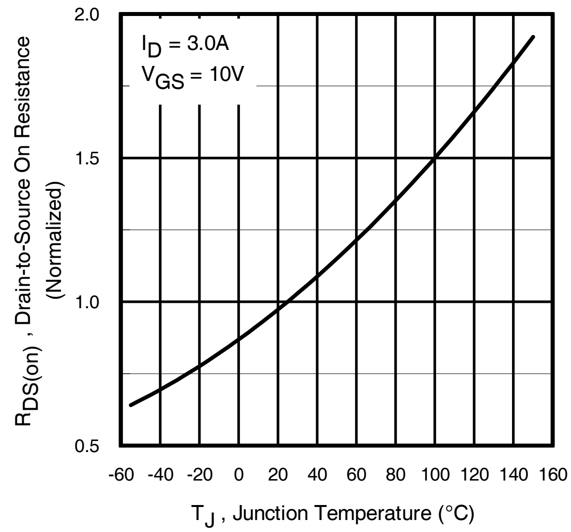
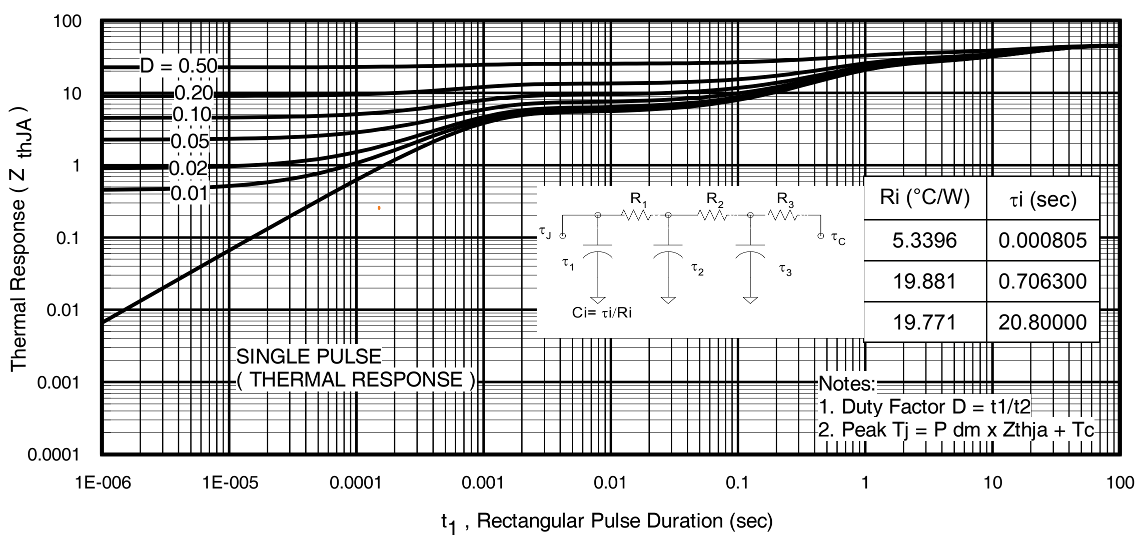


Fig 10. Normalized On-Resistance vs. Temperature



Ri (°C/W)	τi (sec)
5.3396	0.000805
19.881	0.706300
19.771	20.80000

Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

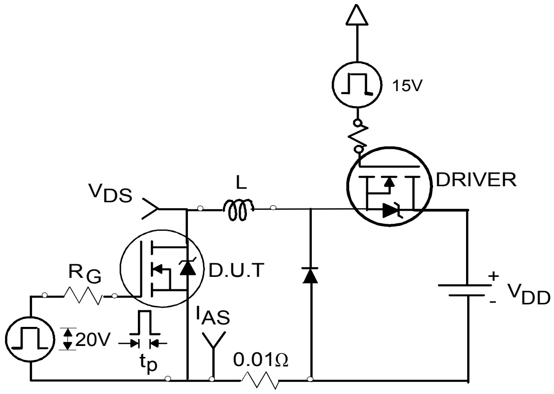


Fig 12a. Unclamped Inductive Test Circuit

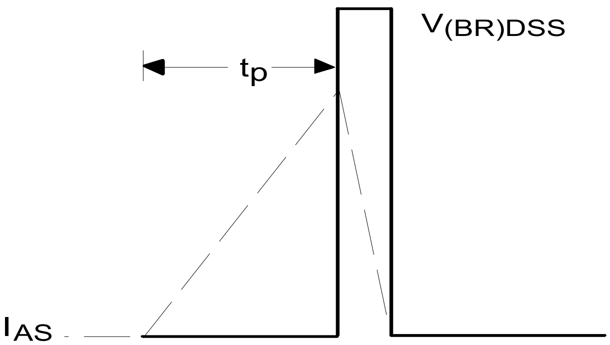


Fig 12b. Unclamped Inductive Waveforms

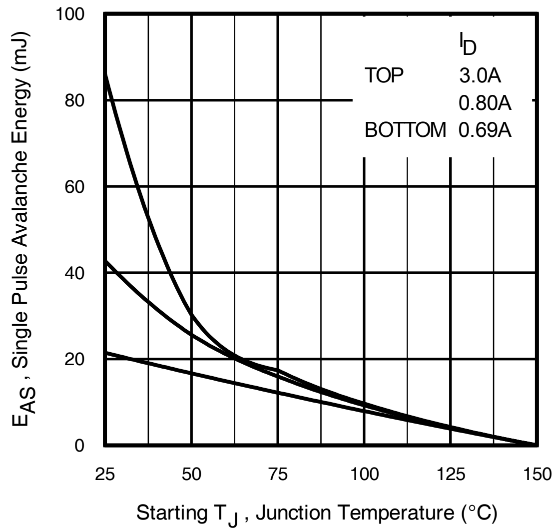


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

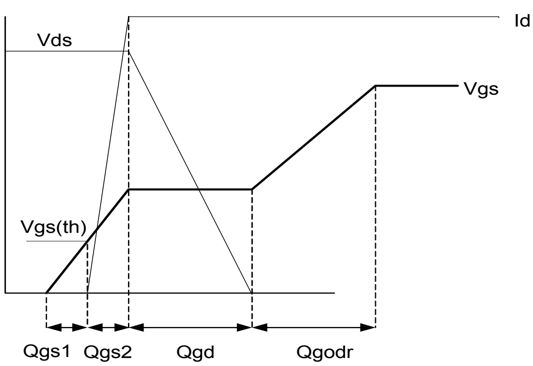


Fig 13a. Basic Gate Charge Waveform

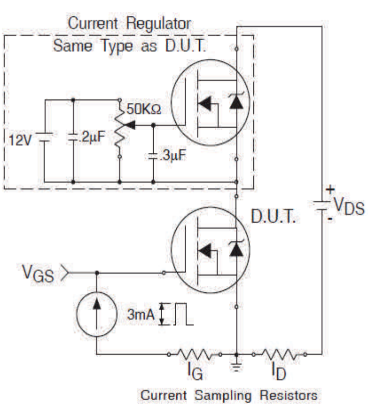


Fig 13b. Gate Charge Test Circuit

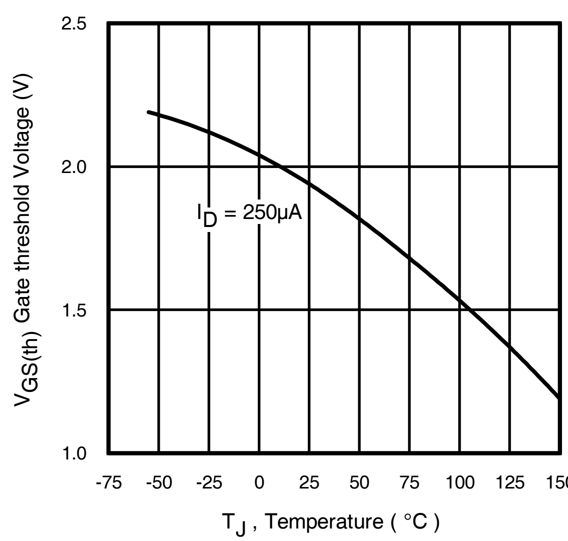


Fig 14. Threshold Voltage vs. Temperature

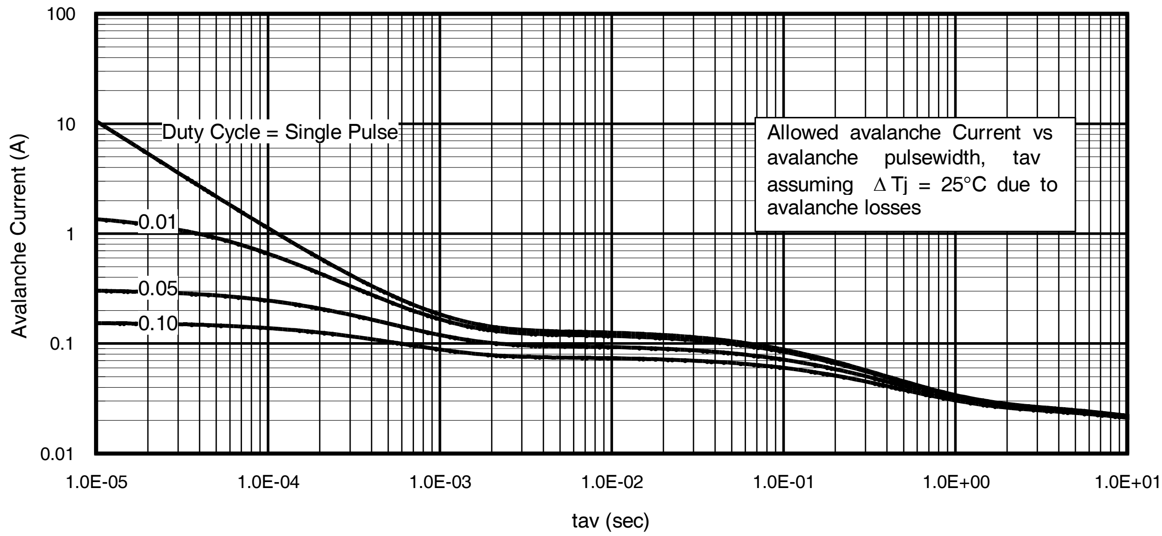


Fig 15. Typical Avalanche Current vs. Pulse width

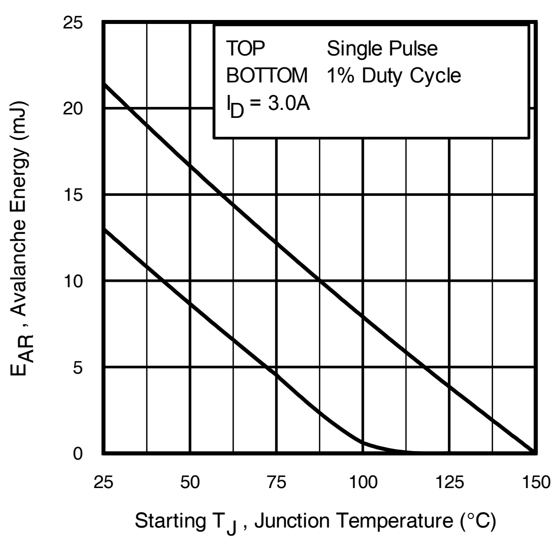


Fig 16. Maximum Avalanche Energy vs. Temperature

Notes on Repetitive Avalanche Curves , Figures 15, 16:
(For further info, see AN-1005 at www.infineon.com)

1. Avalanche failures assumption:
   Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax}. This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 12a, 12b.
4. $P_{D\ (ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 14, 15).
   t_{av} = Average time in avalanche.
   D = Duty cycle in avalanche = $t_{av} \cdot f$
   $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see Figures 13)

$$\mathbf{P_{D\ (ave)} = 1/2\ (\ 1.3 \cdot BV \cdot I_{av}) = \Delta T /\ Z_{thJC}}$$
$$\mathbf{I_{av} = 2\Delta T /\ [1.3 \cdot BV \cdot Z_{th}]}$$
$$\mathbf{E_{AS\ (AR)} = P_{D\ (ave)} \cdot t_{av}}$$

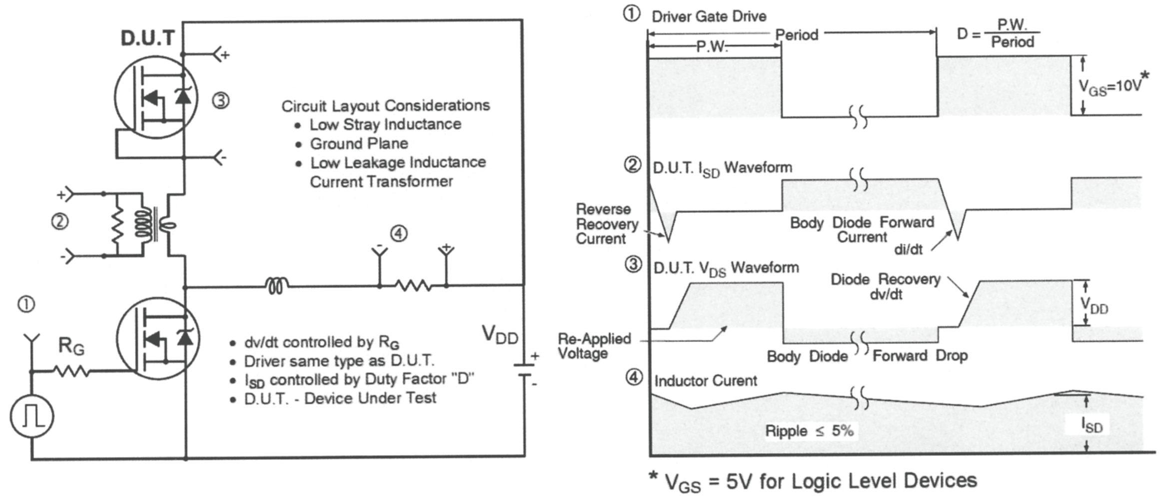


Fig 17. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

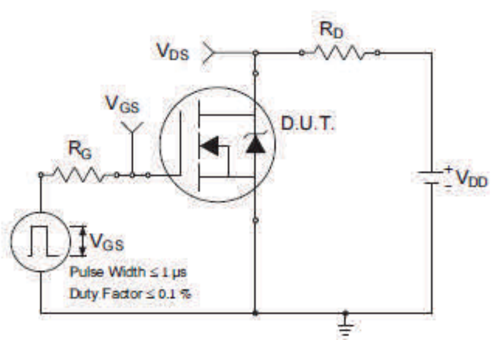


Fig 18a. Switching Time Test Circuit

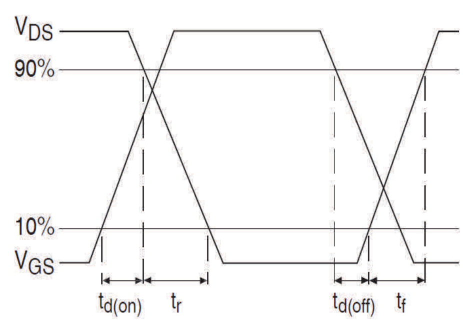
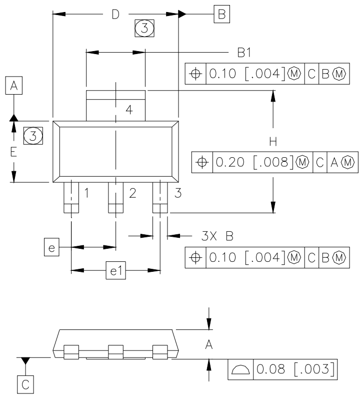
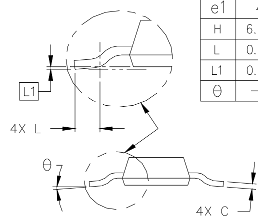


Fig 18b. Switching Time Waveforms

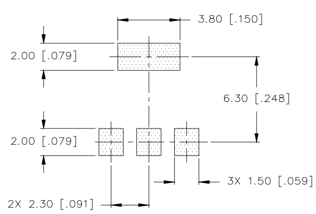
SOT-223 (TO-261AA) Package Outline (Dimensions are shown in millimeters (inches))





DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.55	1.80	.061	.071
B	0.65	0.85	.026	.033
B1	2.95	3.15	.116	.124
C	0.25	0.35	.010	.014
D	6.30	6.70	.248	.264
E	3.30	3.70	.130	.146
e	2.30 BSC		.0905 BSC	
e1	4.60 BSC		.181 BSC	
H	6.71	7.29	.264	.287
L	0.91	—	.036	—
L1	0.061 BSC		.0024 BSC	
θ	—	10°	—	10°

MINIMUM RECOMMENDED FOOTPRINT

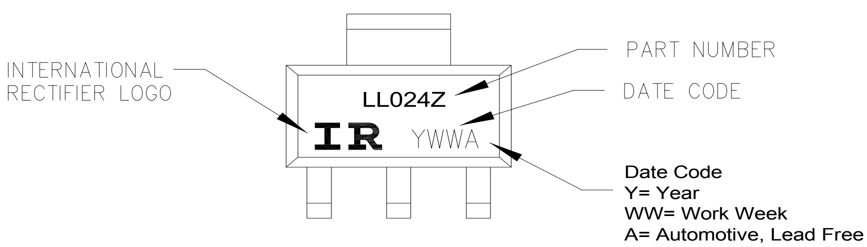


LEAD ASSIGNMENTS

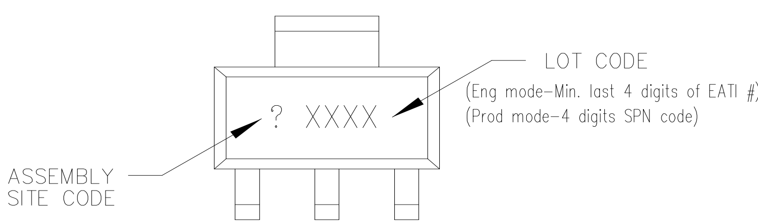
1 = GATE
2 = DRAIN
3 = SOURCE
4 = DRAIN

NOTES:
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M–1994.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS DO NOT INCLUDE MOLD FLASH.
4. OUTLINE CONFORMS TO JEDEC OUTLINE TO–261AA.
5. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].

SOT-223(TO-261AA) Part Marking Information



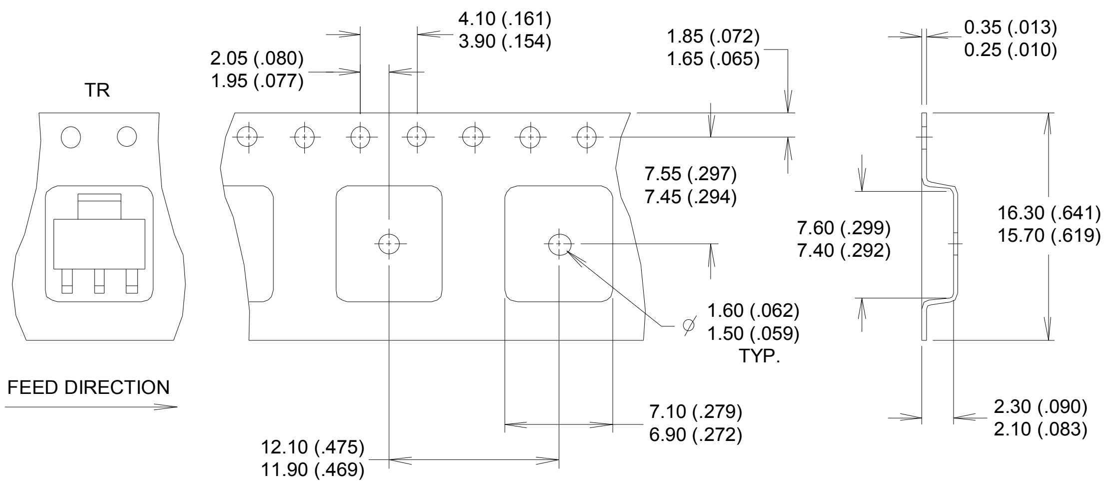
TOP MARKING



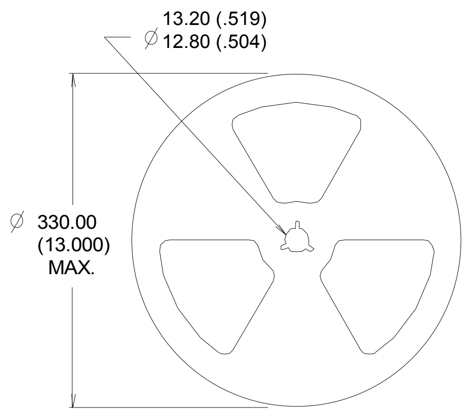
BOTTOM MARKING

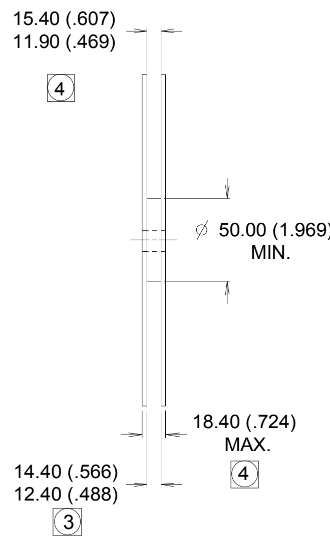
Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

SOT-223(TO-261AA) Tape and Reel (Dimensions are shown in millimeters (inches))



NOTES :
1. CONTROLLING DIMENSION: MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.
3. EACH Ø330.00 (13.00) REEL CONTAINS 2,500 DEVICES.





NOTES :
1. OUTLINE COMFORMS TO EIA-418-1.
2. CONTROLLING DIMENSION: MILLIMETER..
3. DIMENSION MEASURED @ HUB.
4. INCLUDES FLANGE DISTORTION @ OUTER EDGE.

Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

Qualification Information

Qualification Level		Automotive (per AEC-Q101)	
		Comments: This part number(s) passed Automotive qualification. Infineon's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
Moisture Sensitivity Level		SOT-223	MSL1
ESD	Machine Model	Class M1B (+/- 100V)† AEC-Q101-002	
	Human Body Model	Class H0 (+/- 250V)† AEC-Q101-001	
	Charged Device Model	Class C5 (+/- 1125V)† AEC-Q101-005	
RoHS Compliant		Yes	

† Highest passing voltage.

Revision History

Date	Comments
3/26/2014	• Added "Logic Level Gate Drive" bullet in the features section on page 1 • Updated part marking on page 9 • Updated data sheet with new IR corporate template
10/29/2015	• Updated datasheet with corporate template • Corrected ordering table on page 1.

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